

- V_{DS} 100V
- I_D 45A
- $R_{DS(ON)}$ (at $V_{GS}=10V$) 17m Ω
- $R_{DS(ON)}$ (at $V_{GS}=4.5V$) 21.5m Ω
- 100% UIS Tested
- 100% V_{DS} Tested

- Low $R_{DS(on)}$ & FOM
- Extremely low switching loss
- Excellent stability and uniformity
- Fast switching and soft recovery
- Part no. with suffix "Q" means AEC-Q101 qualified

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply
- DC-DC convertor

($T_A=25$ unless otherwise noted)

Drain-source Voltage		V_{DS}	100	V
Gate-source Voltage		V_{GS}	± 20	V
Drain Current	$T_A=25^\circ C$	I_D	7	A
	$T_A=100^\circ C$		4.5	
	$T_C=25^\circ C$		45	
	$T_C=100^\circ C$		28	
Pulsed Drain Current ^A		I_{DM}	180	A
Avalanche energy ^B		EAS	90	mJ
Total Power Dissipation ^C	$T_A=25^\circ C$	P_D	2.5	W
	$T_A=100^\circ C$		1	
	$T_C=25^\circ C$		73	
	$T_C=100^\circ C$		29	
Junction and Storage Temperature Range		T_J, T_{STG}	-55 +150	$^\circ C$



■

Thermal Resistance Junction-to-Ambient ^D	Steady-State	$R_{\theta JA}$	40	50	°C/W
Thermal Resistance Junction-to-Case	Steady-State	$R_{\theta JC}$	1.4	1.7	

(Example)

■

YJD45G10AQ	F1	YJD45G10A	2500	/	25000	13"Reel



($T_J=25$ unless otherwise noted)

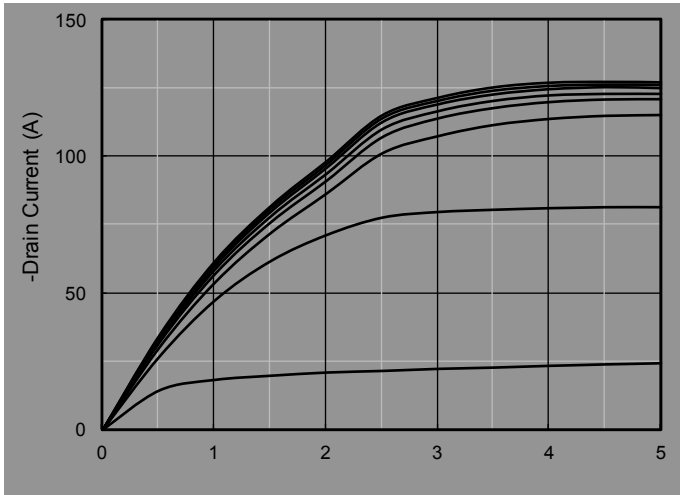
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	100	-	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=100V, V_{GS}=0V$	-	-	1	μA
		$V_{DS}=100V, V_{GS}=0V, T_J=150^\circ C$	-	-	100	
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1.0	1.8	2.5	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=22.5A$	-	14	17	m Ω
		$V_{GS}=4.5V, I_D=20A$	-	17	21.5	
Diode Forward Voltage	V_{SD}	$I_S=22.5A, V_{GS}=0V$	-	0.9	1.2	V
Maximum Body-Diode Continuous Current	I_S		-	-	45	A
Gate resistance	R_G	f=1MHz, Open drain	-	1.4	-	Ω
Input Capacitance	C_{iss}	$V_{DS}=50V, V_{GS}=0V, f=1MHz$	-	1165	-	pF
Output Capacitance	C_{oss}		-	265	-	
Reverse Transfer Capacitance	C_{rss}		-	8	-	
Total Gate Charge	Q_g	$V_{GS}=10V, V_{DS}=50V, I_D=22.5A$	-	19	-	nC
Gate-Source Charge	Q_{gs}		-	6	-	
Gate-Drain Charge	Q_{gd}		-	3	-	
Reverse Recovery Charge	Q_{rr}	$I_F=22.5A, di/dt=100A/us$	-	45	-	nC
Reverse Recovery Time	t_{rr}		-	40	-	ns
Turn-on Delay Time	$t_{D(on)}$	$V_{GS}=10V, V_{DD}=50V, I_D=22.5A$ $R_{GEN}=2.2\Omega$	-	40	-	ns
Turn-on Rise Time	t_r		-	12	-	
Turn-off Delay Time	$t_{D(off)}$		-	55	-	
Turn-off fall Time	t_f		-	16	-	

A. Repetitive rating; pulse width limited by max. junction temperature.

B. $T_J=25^\circ C, V_{DD}=50V, V_G=10V, R_G=25\Omega, L=0.5mH, I_{AS}=19A$.

C. P_d is based on max. junction temperature, using junction-case thermal resistance.

D. The value of $R_{\theta JA}$ is measured with the device mounted on the minimum recommend pad size, in the still air environment with $T_A=25^\circ C$. The maximum allowed junction temperature of $150^\circ C$. The value in any given application depends on the user's specific board design.



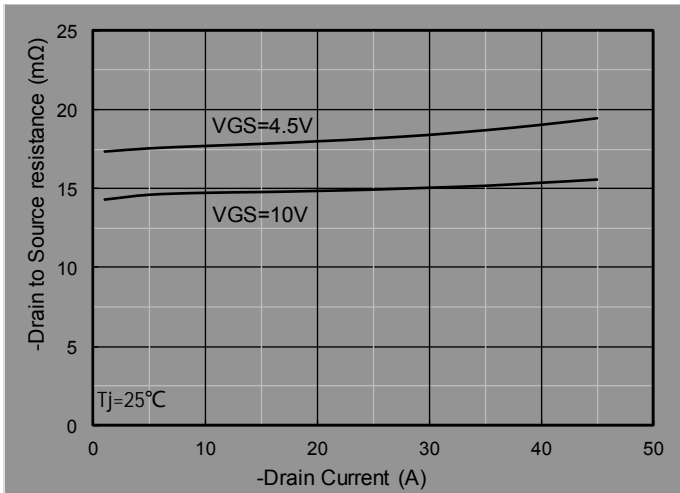


Figure 7. $R_{DS(on)}$ VS Drain Current

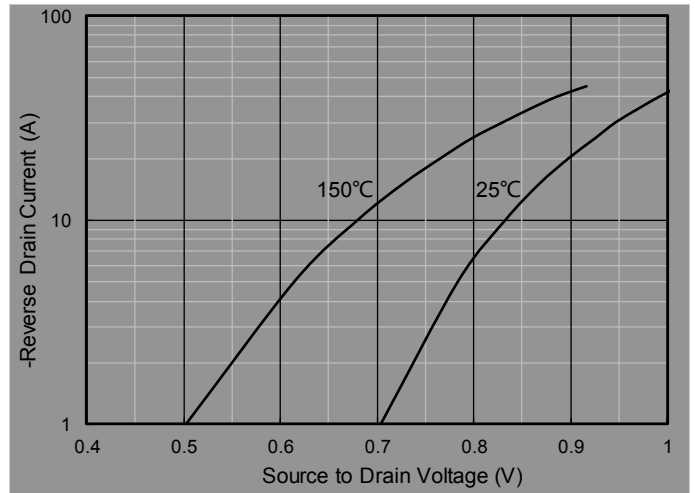


Figure 8. Forward characteristics

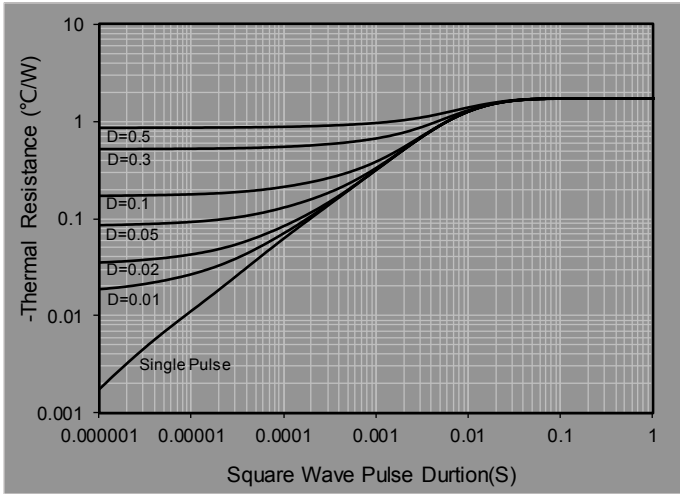


Figure 13. Maximum Transient Thermal Impedance

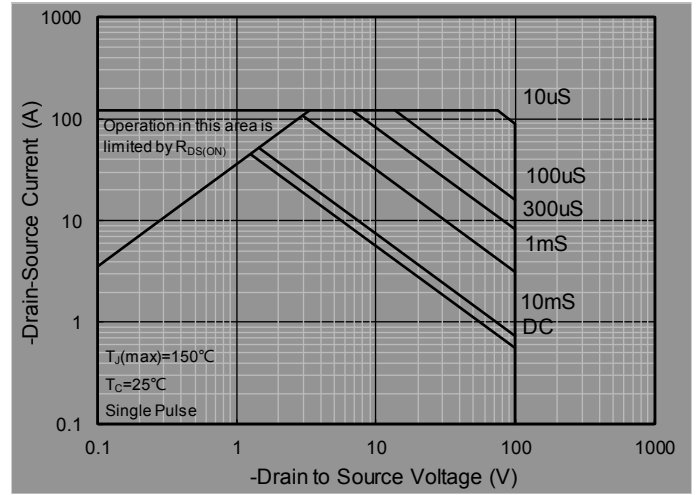


Figure 14. Safe Operation Area

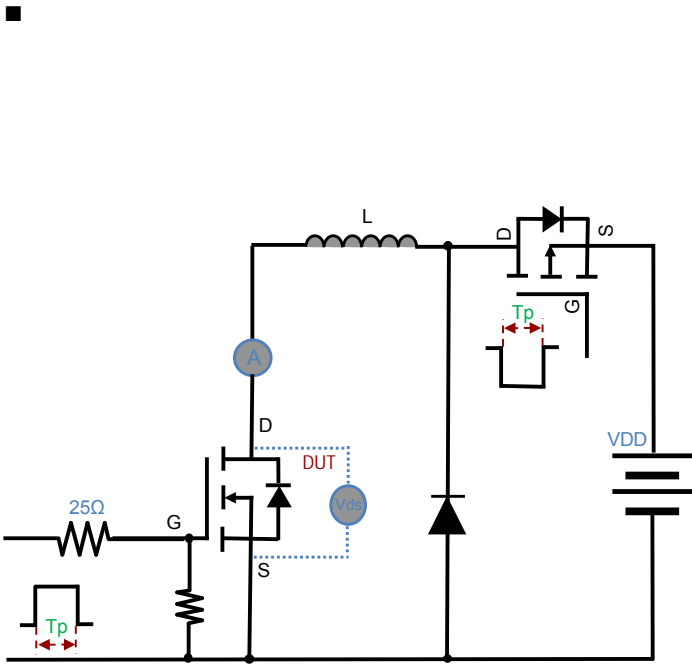
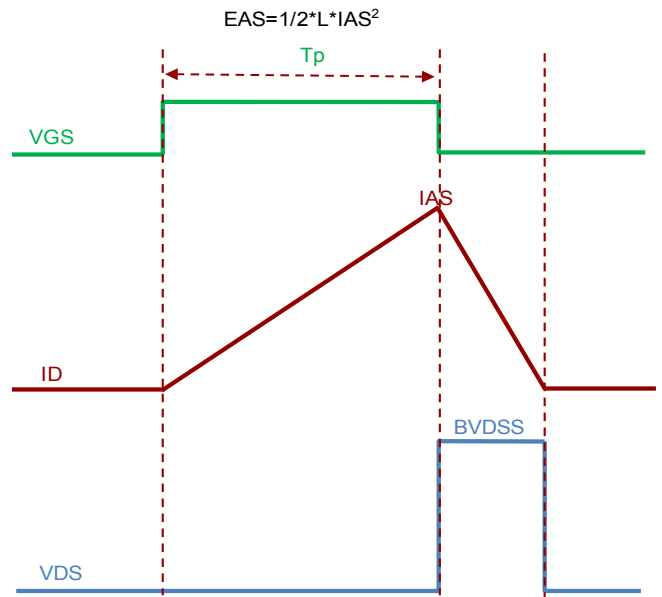


Figure A. Unclamped Inductive Switching (UIS) Test Circuit & Waveform



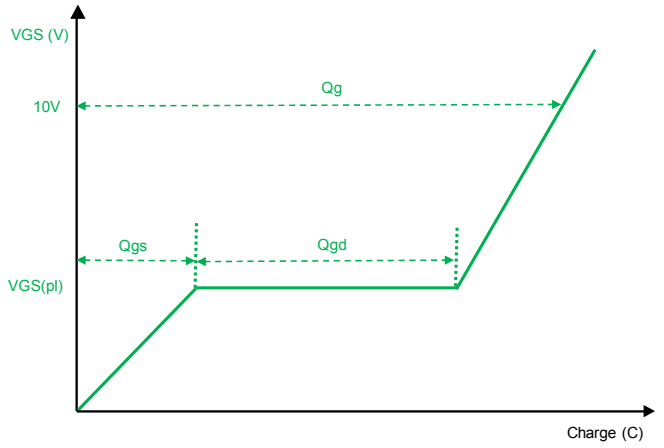
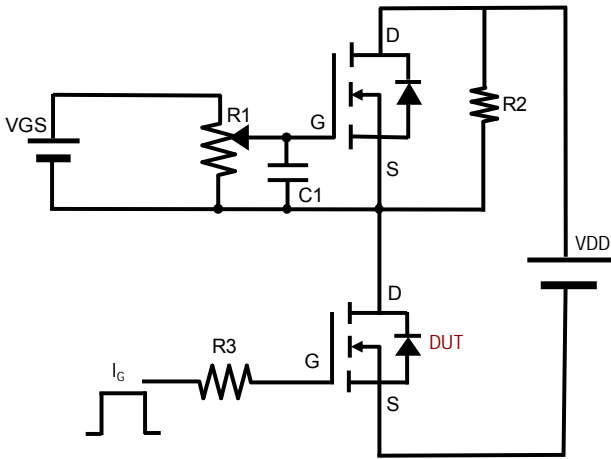


Figure B. Gate Charge Test Circuit & Waveform

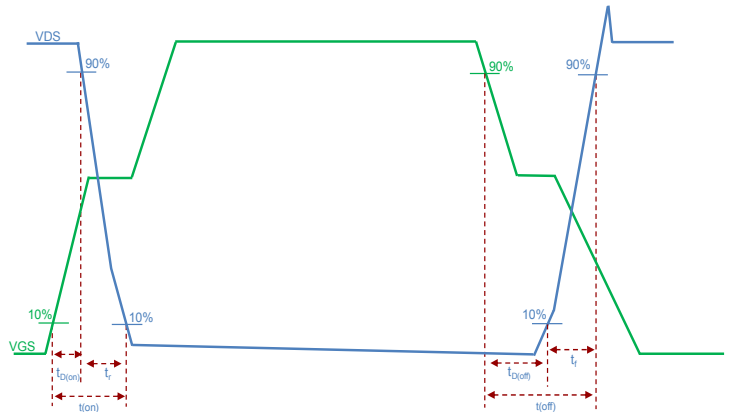
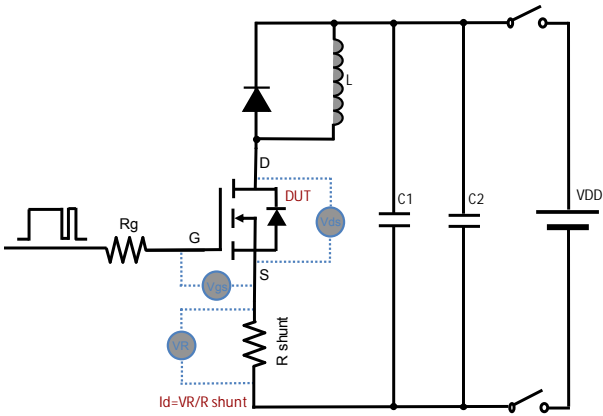


Figure C. Resistive Switching Test Circuit & Waveform

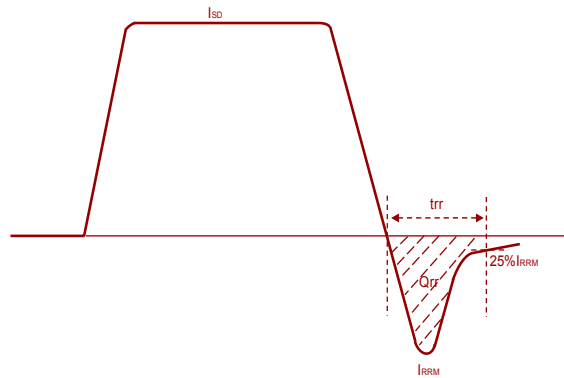
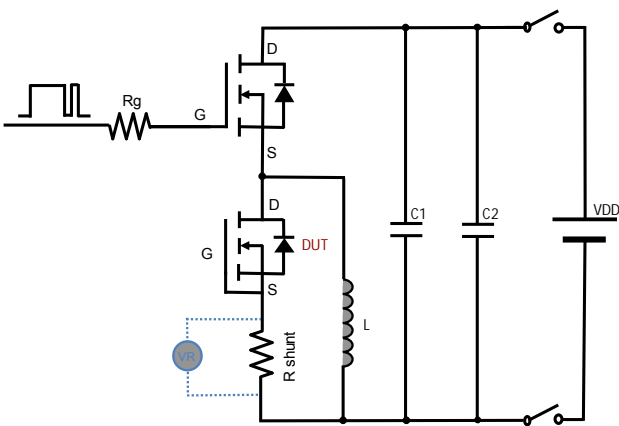
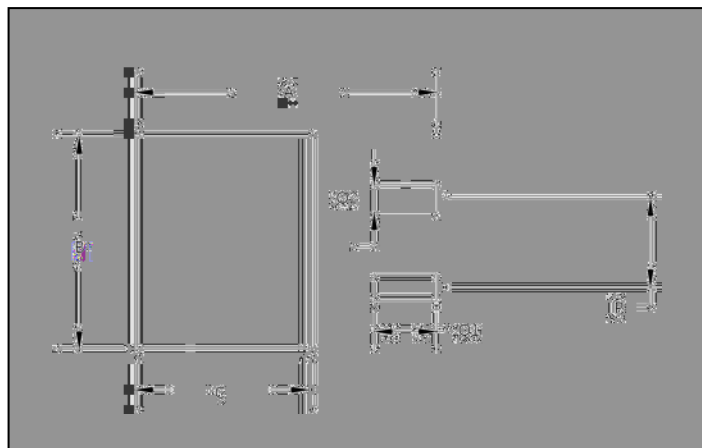
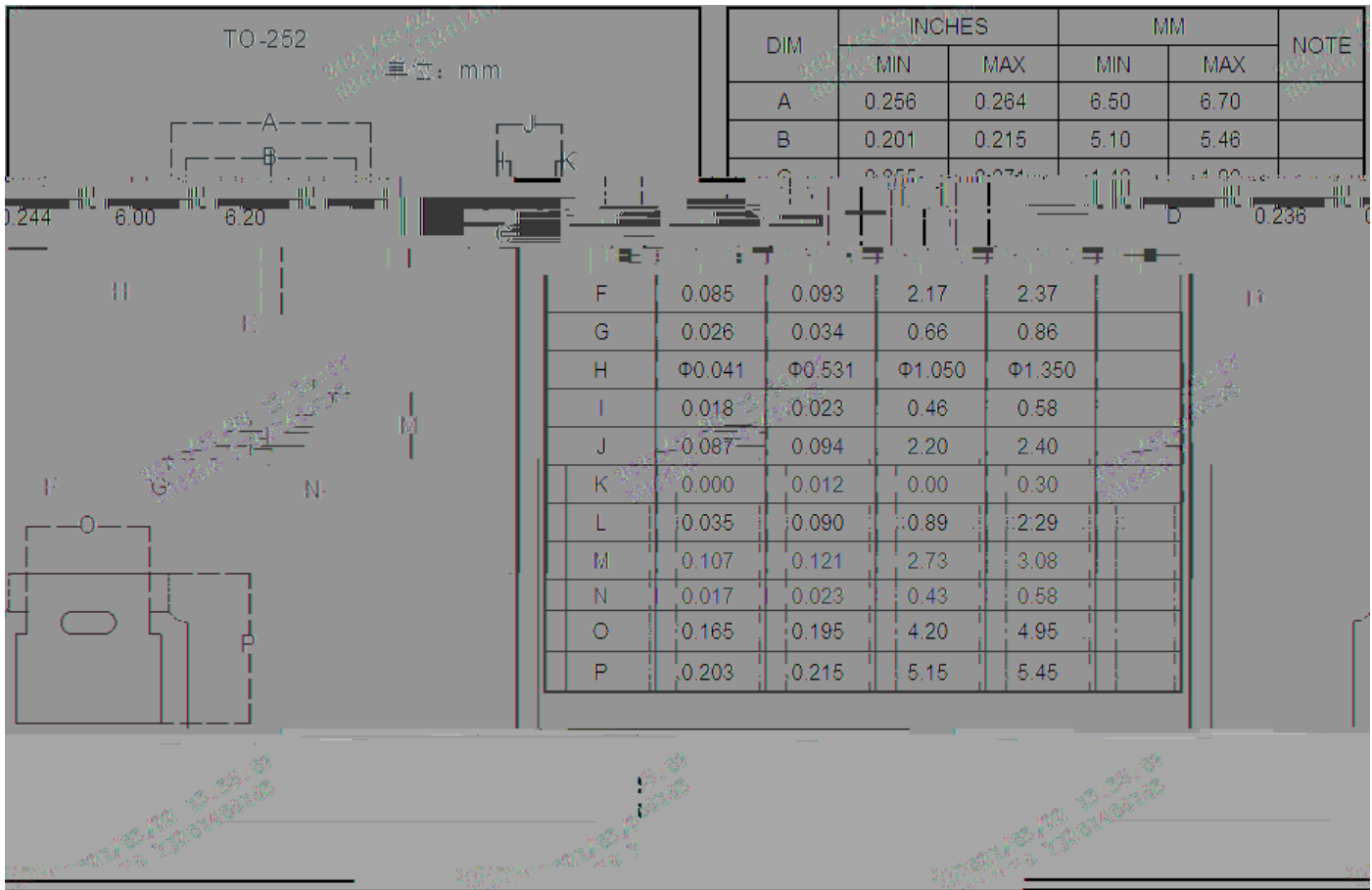


Figure D. Diode Recovery Test Circuit & Waveform



A	11.4
B	6.74
C	6.23
P	4.56
Q1	2.28
Q2	1.52